

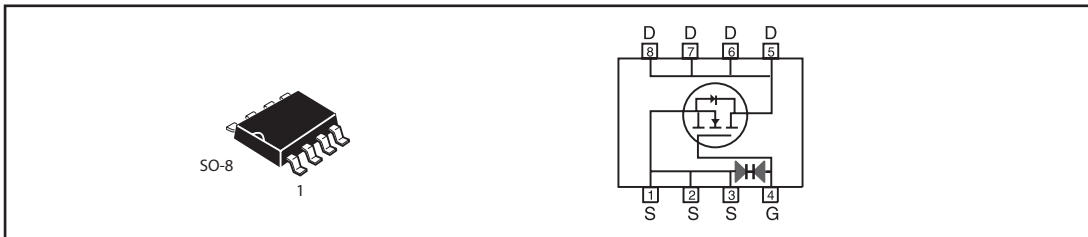


N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
40V	10A	10.5 @ V _{GS} = 10V
		13.5 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (T_A=25 C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous ^a @T _J =25°C -Pulsed ^b	I _D	10	A
	I _{DM}	39	A
Drain-Source Diode Forward Current ^a	I _S	1.7	A
Maximum Power Dissipation ^a	P _D	2.5	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R θJA	50	°C/W
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =32V, V _{GS} =0V			1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±10	uA
ON CHARACTERISTICS^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1	1.8	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A		9	10.5	m ohm
		V _{GS} =4.5V, I _D =6A		11.5	13.5	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} =10V, V _{GS} =10V	20			A
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =10A		23		S
DYNAMIC CHARACTERISTICS^c						
Input Capacitance	C _{ISS}	V _{DS} =20V, V _{GS} =0V f=1.0MHz		1200		pF
Output Capacitance	C _{OSS}			230		pF
Reverse Transfer Capacitance	C _{RSS}			150		pF
SWITCHING CHARACTERISTICS^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =15V I _D =1A V _{GS} =10V R _{GEN} =6 ohm		19		ns
Rise Time	t			20		ns
Turn-Off Delay Time	t _{D(OFF)}			62		ns
Fall Time	t			15		ns
Total Gate Charge	Q _g	V _{DS} =15V, I _D =10A, V _{GS} =10V		22		nC
		V _{DS} =15V, I _D =10A, V _{GS} =4.5V		10		nC
Gate-Source Charge	Q _{gs}	V _{DS} =15V, I _D =10A		2.6		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V		5.5		nC

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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS^b						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 1.7A		0.73	1.2	V

Notes

- a. Surface Mounted on FR4 Board, t ≤ 10sec.
- b. Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- c. Guaranteed by design, not subject to production testing.

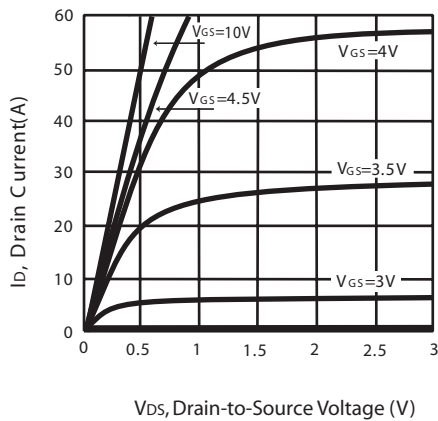


Figure 1. Output Characteristics

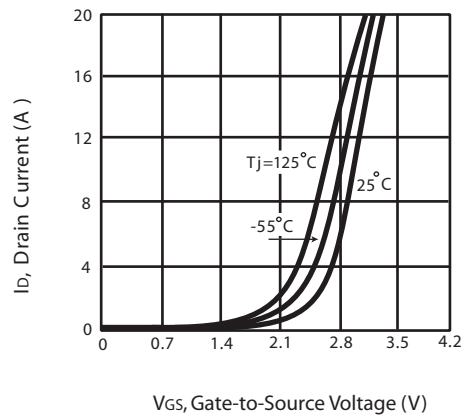


Figure 2. Transfer Characteristics

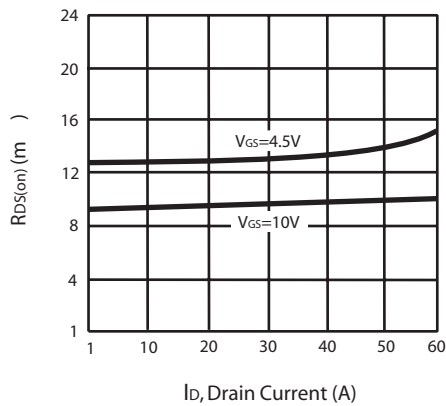


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

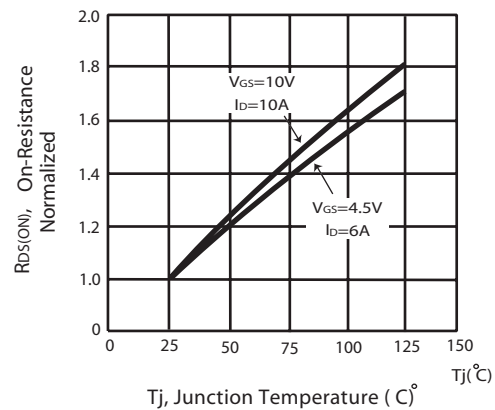


Figure 4. On-Resistance Variation with Drain Current and Temperature

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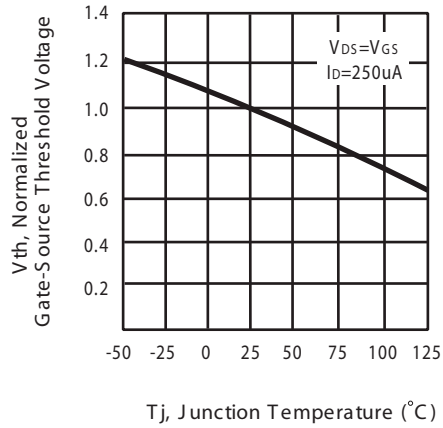


Figure 5. Gate Threshold Variation with Temperature

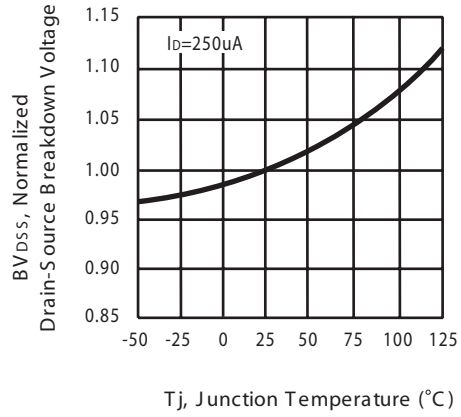


Figure 6. Breakdown Voltage Variation with Temperature

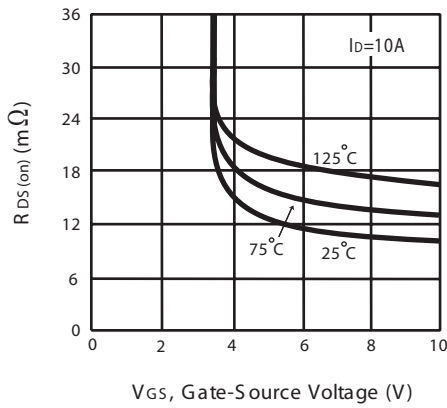


Figure 7. On-Resistance vs. Gate-Source Voltage

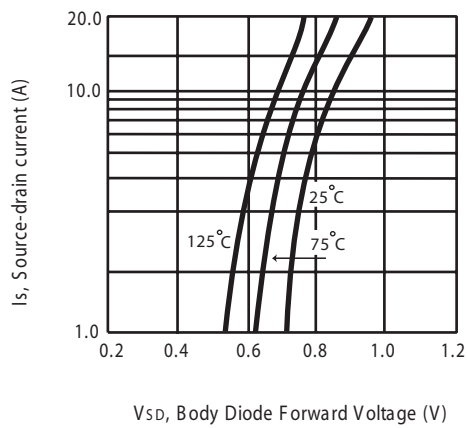


Figure 8. Body Diode Forward Voltage Variation with Source Current

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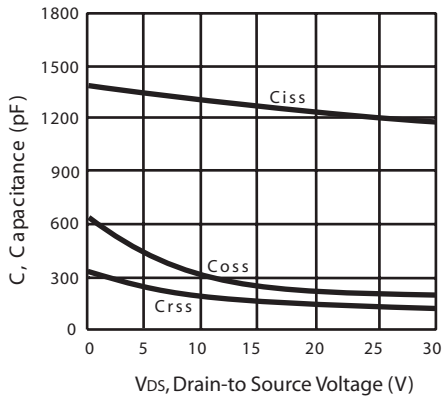


Figure 9. Capacitance

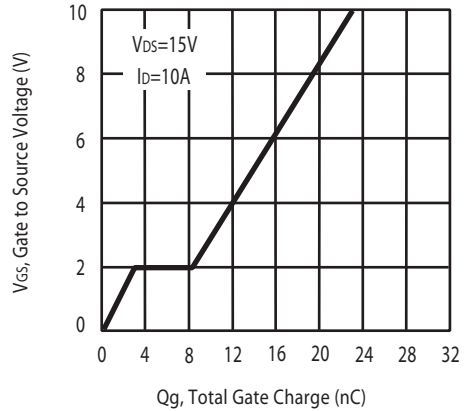


Figure 10. Gate Charge

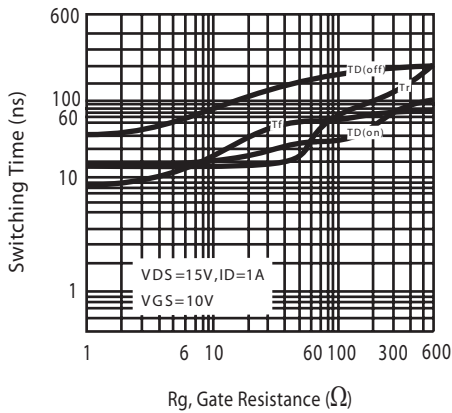


Figure 11. switching characteristics

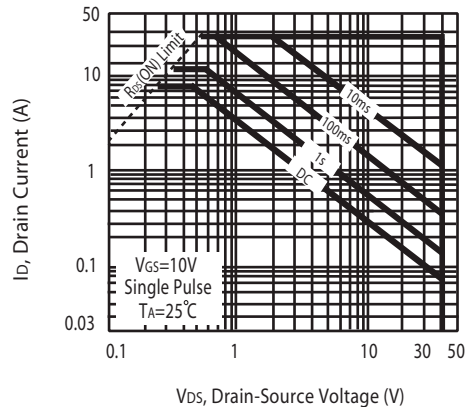
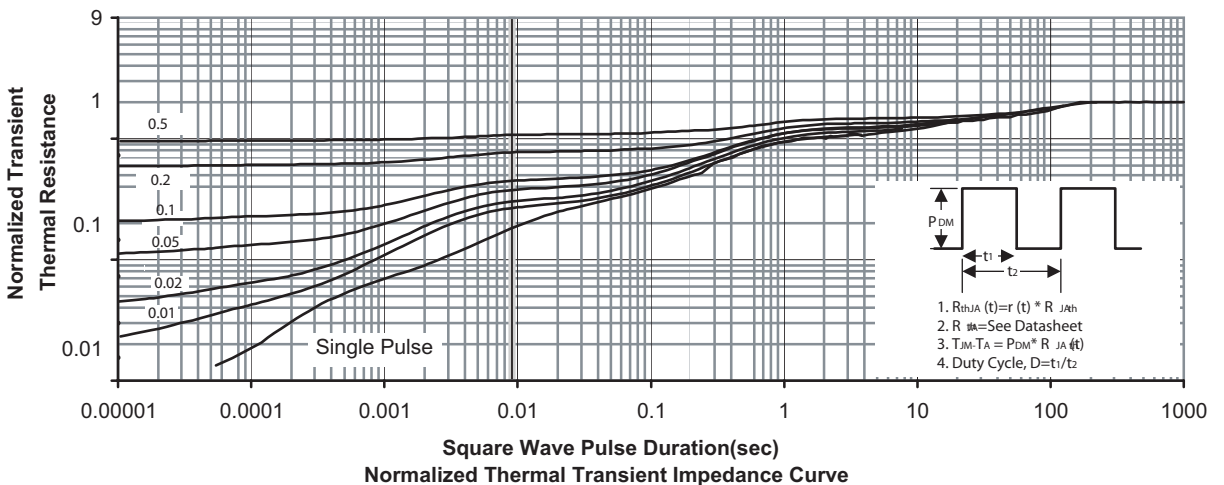


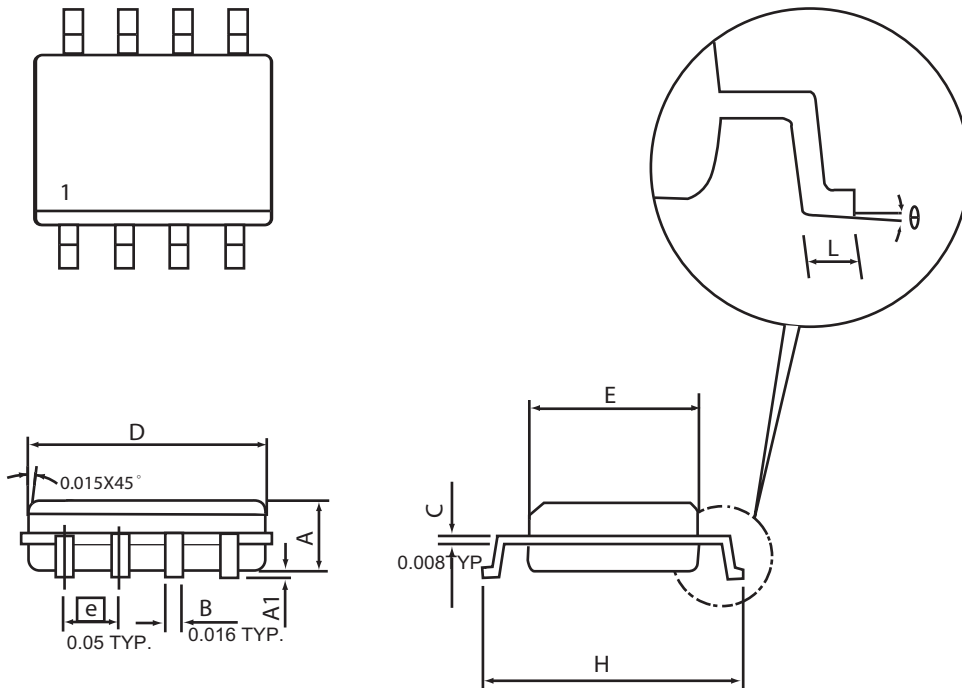
Figure 12. Maximum Safe Operating Area



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PACKAGE OUTLINE DIMENSIONS

SO-8

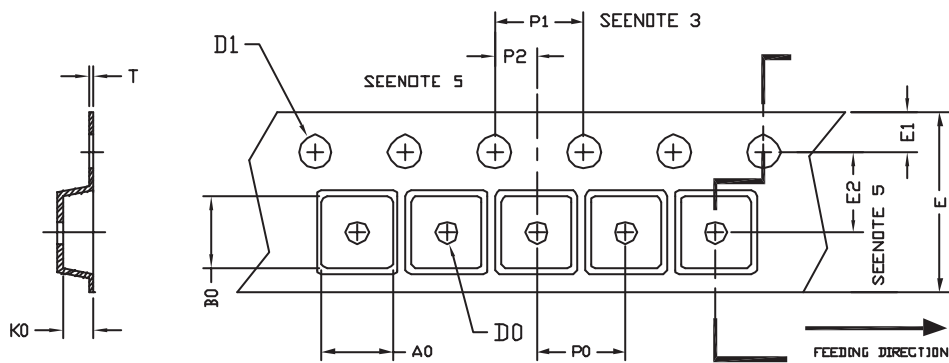


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

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SO-8 Tape and Reel Data

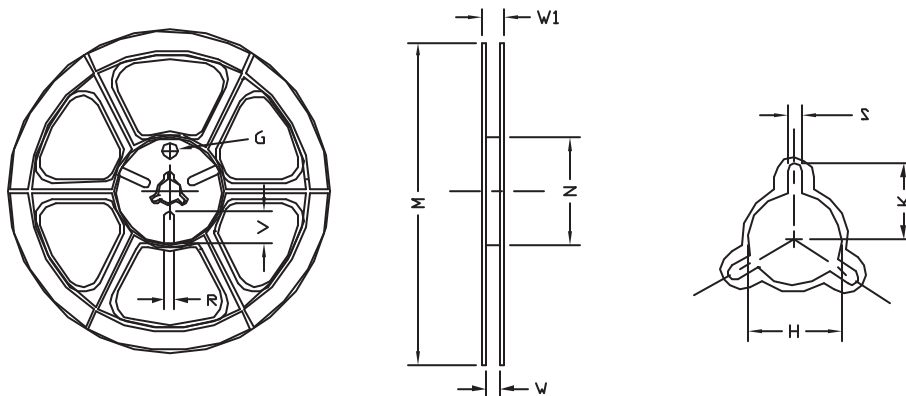
SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5 + 0.1$	$12.0 - 0.0$ ± 0.3	1.75	5.5 ± 0.05	8.0	4.0	2.0 ± 0.05	0.3 ± 0.05

SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 ± 1	62 ± 1.5	$12.4 + 0.2$	$16.8 - 0.4$	$\phi 12.75 + 0.15$	---	2.0 ± 0.15	---	---	---